

(2) D

NCE N-Channel Super Trench Power MOSFET

Description

The NCEP01T12D uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

General Features

- V_{DS} =100V,I_D =129A
 R_{DS(ON)} <5.0mΩ @ V_{GS}=10V
- Excellent gate charge x R_{DS(on)} product
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

100% UIS TESTED!

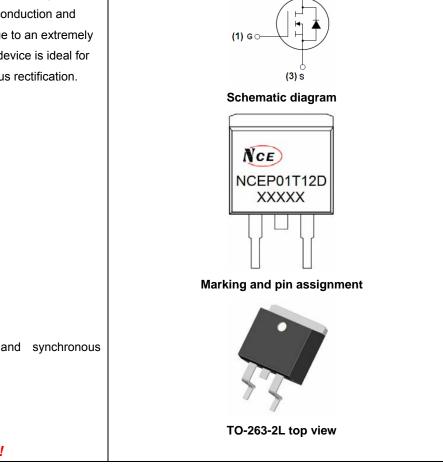
100% ΔVds TESTED!

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP01T12D	NCEP01T12D	TO-263-2L	-	-	-

Absolute Maximum Ratings (T_c=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	Vds	100	V	
Gate-Source Voltage	V _{GS}	±20	V	
Drain Current-Continuous	Ι _D	129	А	
Drain Current-Continuous(Tc=100℃)	I _D (100℃)	92	А	
Pulsed Drain Current	I _{DM}	480	А	
Maximum Power Dissipation	PD	185	W	
Derating factor		1.3	W/℃	
Single pulse avalanche energy (Note 5)	E _{AS}	1000	mJ	
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 175	°C	





Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	R _{θJC}	0.7	°C/W
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Electrical Characteristics (T_C=25[°]C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	····					
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	100		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±20V, V_{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, I _D =250µA	2.5		4.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =60A	-	4.5	5.0	mΩ
Forward Transconductance	g fs	V _{DS} =10V,I _D =60A	60	-	-	S
Dynamic Characteristics (Note4)			- i	1		
Input Capacitance	Clss		-	5600	-	PF
Output Capacitance	C _{oss}	V _{DS} =50V,V _{GS} =0V, F=1.0MHz	-	641	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHZ	-	28	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	16	-	nS
Turn-on Rise Time	tr	V _{DD} =50V,I _D =60A	-	67	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{G} =4.7 Ω	-	45	-	nS
Turn-Off Fall Time	t _f		-	14	-	nS
Total Gate Charge	Qg)/ _ = = 0)/ _ = 00.0	-	84.7		nC
Gate-Source Charge	Q _{gs}	V _{DS} =50V,I _D =60A, V _{GS} =10V	-	30.6		nC
Gate-Drain Charge	Q _{gd}	V _{GS} -10V	-	18.3		nC
Drain-Source Diode Characteristics			·			•
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =129A	-		1.2	V
Diode Forward Current (Note 2)	I _S		-	-	129	Α
Reverse Recovery Time	trr	T_J = 25°C, I_F = I_S	-	60		nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	140		nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, t \leq 10 sec.

3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

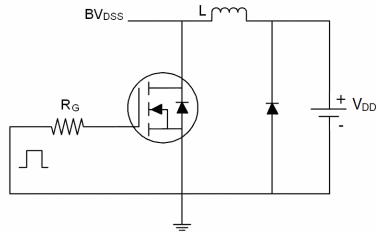
4. Guaranteed by design, not subject to production

5. EAS condition : Tj=25 $^{\circ}$ C,V_{DD}=50V,V_G=10V,L=0.5mH,Rg=25 Ω

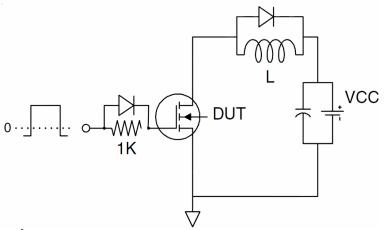


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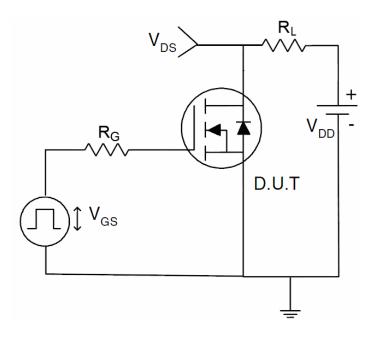
Test Circuit 1) E_{AS} test Circuit



2) Gate charge test Circuit

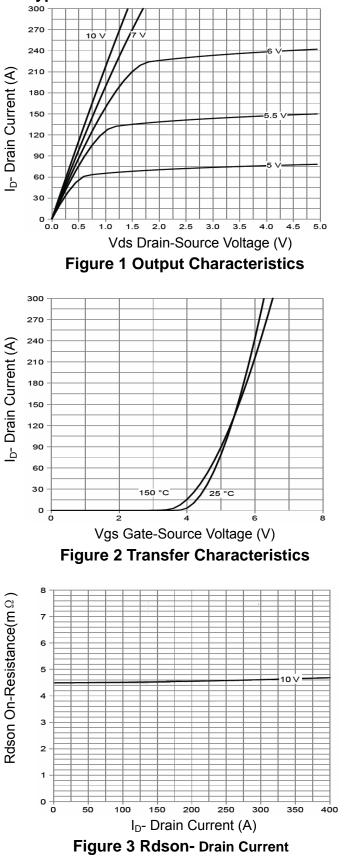


3) Switch Time Test Circuit









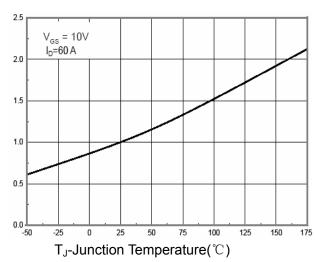
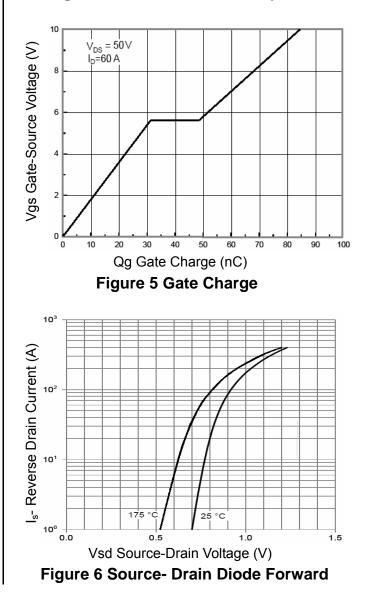


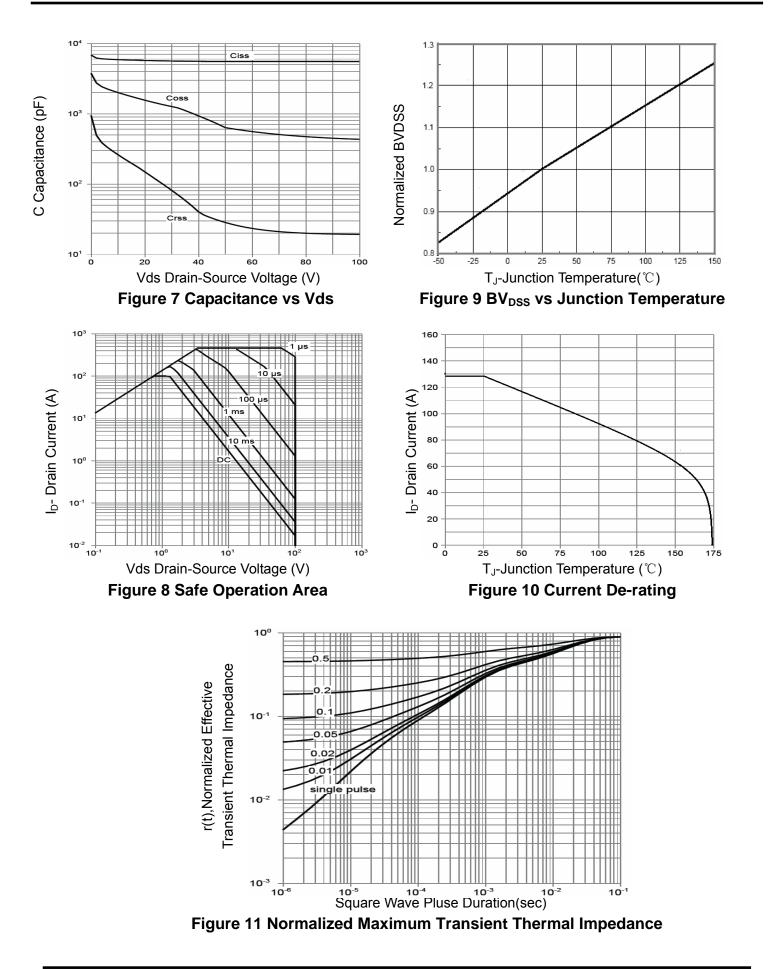
Figure 4 Rdson-JunctionTemperature





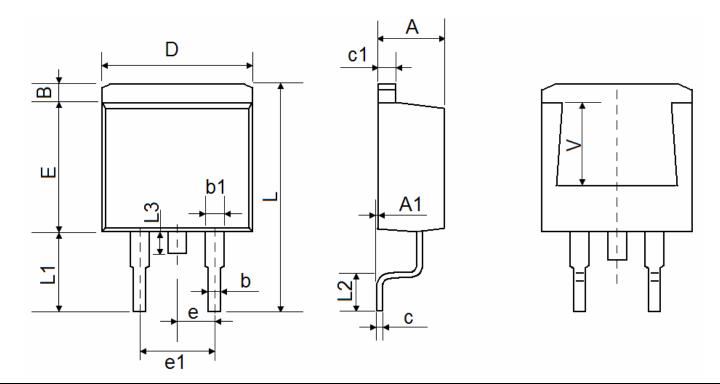
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NCEP01T12D





TO-263-2L Package Information



Symbol	Dimensions I	n Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
A	4.470	4.670	0.176	0.184	
A1	0.000	0.150	0.000	0.006	
В	1.170	1.370	0.046	0.054	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.310	0.530	0.012	0.021	
c1	1.170	1.370	0.046	0.054	
D	10.010	10.310	0.394	0.406	
E	8.500	8.900	0.335	0.350	
е	2.540	TYP.	0.100	TYP.	
e1	4.980	5.180	0.196	0.204	
L	15.050	15.450	0.593	0.608	
L1	5.080	5.480	0.200	0.216	
L2	2.340	2.740	0.092	0.108	
L3	1.300	1.700	0.051	0.067	
V	5.600	REF	REF 0.220 REF		



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